ELECTRONICS, INC.
44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748–5089

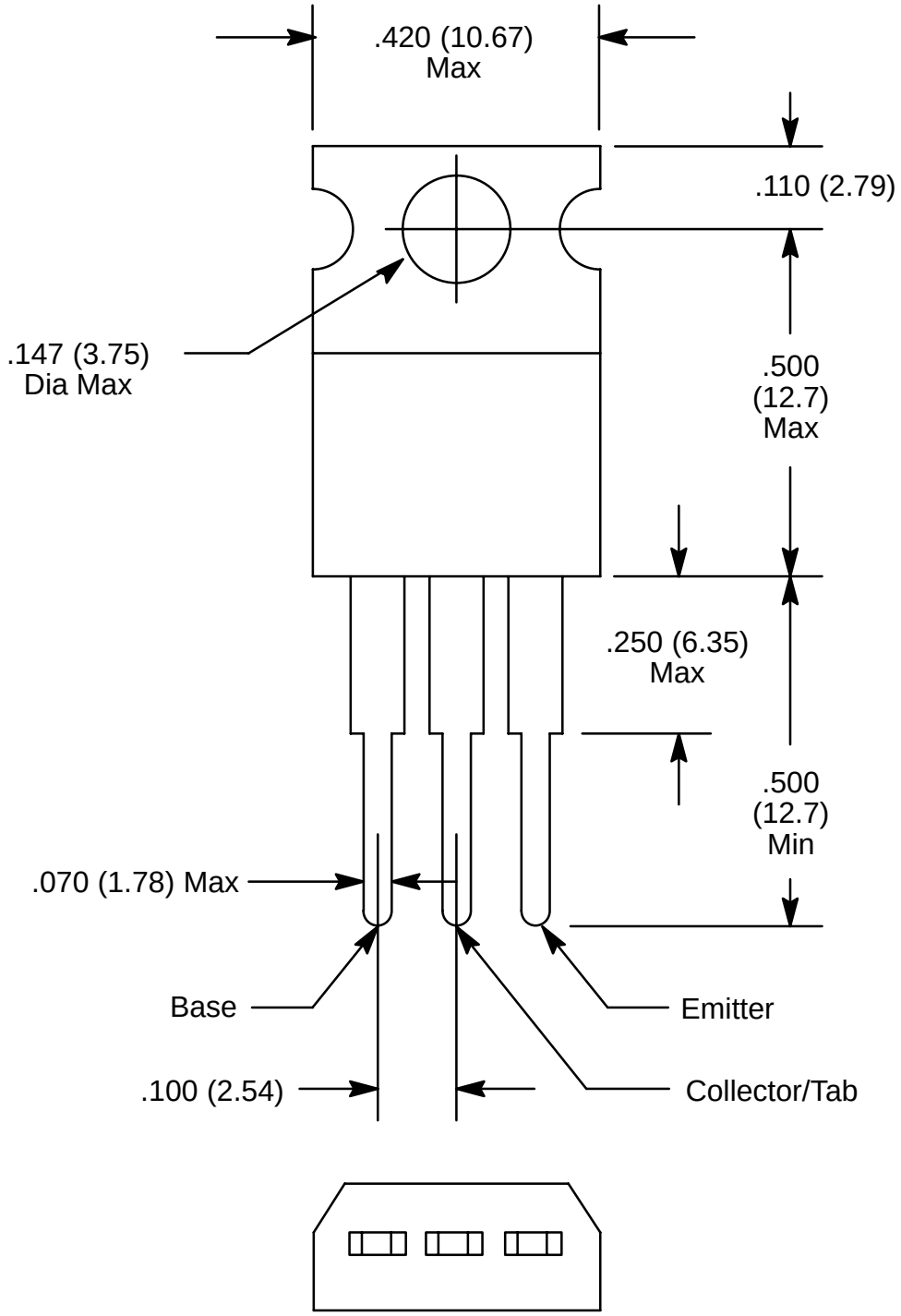
NTE375
Silicon NPN Transistor
TV Vertical Output
(Compl to NTE398)

Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified)

Collector–Base Voltage, V_{CBO} 200V
Collector–Emitter Voltage, V_{CEO} 150V
Emitter–Base Voltage, V_{EBO} 6V
Collector Current, I_C
  Continuous 2A
  Peak 10A
Collector Dissipation (T_A = +25°C), P_C 1.75W
Collector Dissipation (T_C = +25°C), P_C 25W
Operating Junction Temperature, T_J . . . . . +150°C
Storage Temperature Range, T_{stg} . . . . . –40° to +150°C

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	V_{CB} = 180V, I_E = 0	–	–	1.0	mA
Emitter Cutoff Current	I_{EBO}	V_{EB} = 5V, I_C = 0	–	–	5.0	mA
DC Current Gain	h_{FE}	V_{CE} = 2V, I_C = 500mA	100	–	200	
Gain Bandwidth Product	f_T	V_{CE} = 5V, I_C = 500mA	–	8	–	MHz
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 1A, I_B = 100mA	–	–	1.5	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	I_C = 1A, I_B = 100mA	–	–	1.8	V


.420 (10.67)
Max
.110 (2.79)
.147 (3.75)
Dia Max
.500
(12.7)
Max
.250 (6.35)
Max
.500
(12.7)
Min
.070 (1.78) Max
Base
Emitter
.100 (2.54)
Collector/Tab